

Silicon PNP Power Transistors

2SA757

DESCRIPTION

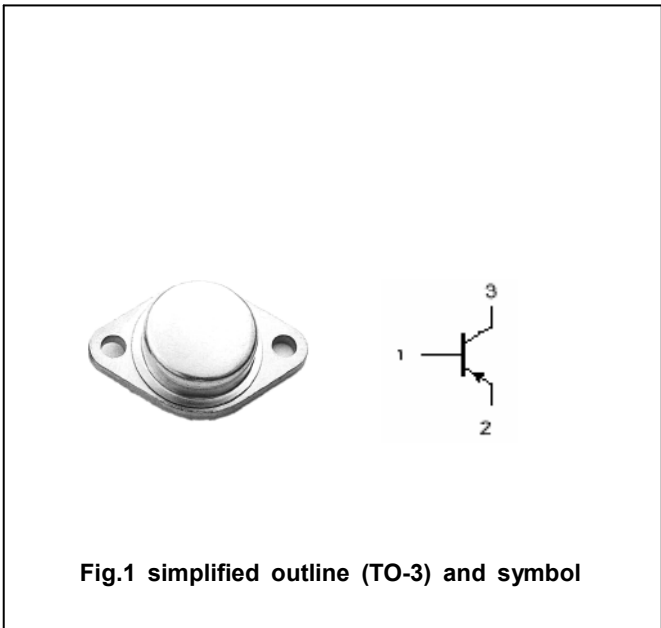
- With TO-3 package
- Complement to type 2SC897

APPLICATIONS

- For audio amplifier power output applications

PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |



Absolute maximum ratings(Ta=□)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|---------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | -120 | V |
| V _{CEO} | Collector-emitter voltage | Open base | -100 | V |
| V _{EBO} | Emitter-base voltage | Open collector | -6 | V |
| I _C | Collector current | | -7 | A |
| I _{CM} | Collector current-peak | | -12 | A |
| P _C | Collector power dissipation | T _C =25□ | 60 | W |
| T _j | Junction temperature | | 150 | □ |
| T _{stg} | Storage temperature | | -55~150 | □ |

Silicon PNP Power Transistors

2SA757

CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-50mA ; R _{BE} =∞ | -100 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =-5mA , I _E =0 | -120 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =-5mA , I _C =0 | -5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-5A ; I _B =-1A | | | -1.8 | V |
| V _{BE} | Base-emitter on voltage | I _C =-1A ; V _{CE} =-5V | | | -1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-30V ; I _E =0 | | | -1 | mA |
| h _{FE-1} | DC current gain | I _C =-1A ; V _{CE} =-5V | 25 | | 200 | |
| h _{FE-2} | DC current gain | I _C =-5A ; V _{CE} =-5V | 20 | | | |
| f _T | Transition frequency | I _C =-1A ; V _{CE} =-5V | | 24 | | MHz |

◆ h_{FE-1} Classifications

| A | B | C |
|-------|--------|---------|
| 25-60 | 50-120 | 100-200 |

PACKAGE OUTLINE

